

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1. (Currently amended) A manufacturing method of a semiconductor device, comprising the steps of:

providing a rigid substrate which supports one or more semiconductor elements on a surface of the substrate and is clamped between an upper mold and a lower mold of an encapsulation mold at a time of resin encapsulation, so that a vent-end edge portion of the substrate corresponding to a vent end of the encapsulation mold has a thickness smaller than a thickness of other portions of the substrate;

disposing the substrate in the encapsulation mold; [[and]]

injecting resin into a cavity between the upper mold and the substrate to encapsulate the semiconductor elements with the resin; and

wherein the substrate is provided so that only a part of the vent-end edge portion of the substrate has a thickness smaller than the thickness of the other portions of the substrate.

2. (Cancelled).

3. (Withdrawn) A manufacturing method of a semiconductor device, comprising the steps of:

providing an encapsulation mold having an upper mold and a lower mold for

clamping a rigid substrate, which supports one or more semiconductor elements on a surface of the substrate, between the upper mold and the lower mold at a time of resin encapsulation, so that the low mold has a void at a vent end of the encapsulation mold which confronts a vent-end edge portion of the substrate;

disposing the substrate in the encapsulation mold; and

injecting resin into a cavity between the upper mold and the substrate to encapsulate the semiconductor elements with the resin.

4. (Withdrawn) A manufacturing method of a semiconductor device, comprising the steps of:

providing a rigid substrate which supports one or more semiconductor elements on a front surface of the substrate and is clamped between an upper mold and a lower mold of an encapsulation mold at a time of resin encapsulation;

attaching a cover film to a back surface of the substrate so that the back surface of the substrate except a vent-end edge portion of the substrate corresponding to a vent end of the encapsulation mold is covered by the cover film so as to form a void at the vent-end edge portion;

disposing the substrate with the cover film in the encapsulation mold; and

injecting resin into a cavity between the upper mold and the substrate to encapsulate the semiconductor elements with the resin.

5. (Withdrawn) A manufacturing method of a semiconductor device, comprising the steps of:

providing an encapsulation mold having an upper mold and a lower mold for clamping a rigid substrate, which supports one or more semiconductor elements on a surface of the substrate, between the upper mold and the lower mold at a time of resin encapsulation;

attaching a release film to a surface of the lower mold so that the surface of the lower mold except a portion confronting a vent-end edge portion of the substrate corresponding to a vent end of the encapsulation mold is covered by the release film so as to form a void at the vent-end edge portion;

disposing the substrate in the encapsulation mold; and

injecting resin into a cavity between the upper mold and the substrate to encapsulate the semiconductor elements with the resin.

6. (Withdrawn) A manufacturing method of a semiconductor device, comprising the steps of:

providing a rigid substrate which supports one or more semiconductor elements on a surface of the substrate and is clamped between an upper mold and a lower mold of an encapsulation mold at a time of resin encapsulation;

forming the substrate with a slit located near a vent-end edge portion of the substrate corresponding to a vent end of the encapsulation mold;

attaching a release film to a surface of the lower mold so that the entire surface of the lower mold is covered by the release film;

disposing the substrate with the slit formed therein in the encapsulation mold; and

injecting resin into a cavity between the upper mold and the substrate to encapsulate the semiconductor elements with the resin.

7. (Withdrawn) A manufacturing method of a semiconductor device, comprising the steps of:

disposing a rigid substrate, which supports one or more semiconductor elements on a surface of the substrate, between an upper mold and a lower mold of an encapsulation mold;

clamping the substrate with the upper mold and the lower mold by setting a clamping pressure to a first pressure that is small enough to allow separation of the upper mold from the substrate surface at a vent-end edge portion of the substrate;

injecting resin into a cavity of the encapsulation mold;

setting, after an end of the resin injection, the clamping pressure to a second pressure that is larger than the first pressure and enough to compress the substrate surface by the upper mold at the vent-end edge portion; and

encapsulating the semiconductor elements supported on the substrate surface with the injected resin.

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8. (New) The manufacturing method of a semiconductor device according to claim 1 wherein said vent-end edge portion is located at least in part in a vent of said encapsulation mold.

9. (New) The manufacturing method of a semiconductor device according to claim 1 wherein said substrate moves within a vent of said encapsulation mold during said injecting step.